

# S22MD1V/S22MD3

## Photothyristor Coupler

\* Lead forming type (I type) and taping reel type (P type) of **S22MD1V** are also available (**S22MD1V/S22MD1P**)

\*\* TÜV (DIN-VDE0884) approved type is also available as an option.

### ■ Features

1. High repetitive peak OFF-state voltage  
( $V_{DRM}$  : MIN. 600V )
2. Low trigger current  
( $I_{FT}$  : MAX. 10mA at  $R_G = 20k\Omega$  )
3. High isolation voltage between input and output

**S22MD1V** ...  $V_{iso}$  : 5 000V<sub>rms</sub>

**S22MD3V** ...  $V_{iso}$  : 2 500V<sub>rms</sub>

\* **S22MD1V** and **S22MD3** are for 200V line.

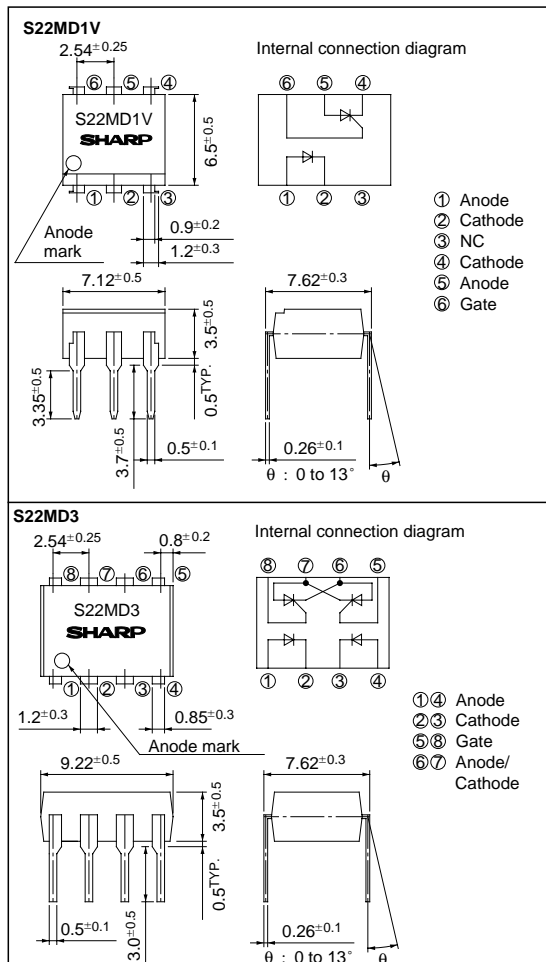
4. Recognized by UL, file NO. 64380

### ■ Applications

1. ON-OFF operation for a low power load
2. For triggering high power thyristor and triac

### ■ Outline Dimensions

(Unit : mm)



## Absolute Maximum Ratings

(Ta = 25°C)

Parameter		Symbol	Rating		Unit
			S22MD1V	S22MD3	
Input	Forward current	I <sub>F</sub>	50		mA
	Reverse voltage	V <sub>R</sub>	6		V
Output	RMS ON-state current	I <sub>T</sub>	200		mA <sub>rms</sub>
	*1Peak one cycle surge current	I <sub>surge</sub>	2		A
	*2Repetitive peak OFF-state voltage	V <sub>DRM</sub>	600		V
	*2Repetitive peak reverse voltage	V <sub>R<sub>RM</sub></sub>	600	-	V
*3Isolation voltage		V <sub>iso</sub>	5 000	2 500	V <sub>rms</sub>
Operating temperature		T <sub>opr</sub>	-30 to +100	-30 to +100	°C
Storage temperature		T <sub>stg</sub>	-55 to +125	-40 to +125	°C
*4Soldering temperature		T <sub>sol</sub>	260		°C

\*1 50H z, sine wave

\*2 R<sub>G</sub> = 20kΩ

\*3 40 to 60% RH, AC for 1 minute

\*4 For 10 seconds

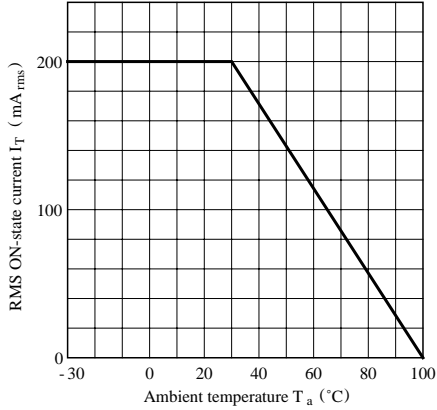
## Electro-optical Characteristics

(Ta = 25°C)

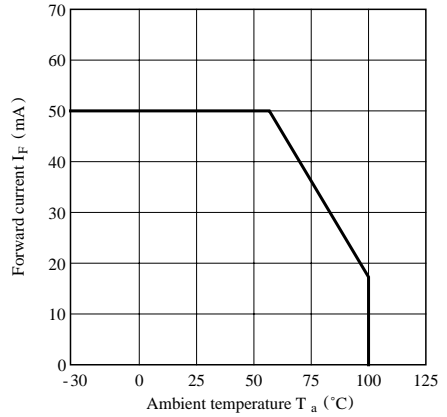
Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V <sub>F</sub>	I <sub>F</sub> = 30mA	-	1.2	1.4	V
	Reverse current	I <sub>R</sub>	V <sub>R</sub> = 3V	-	-	10 <sup>-5</sup>	A
Output	Repetitive peak OFF-state current	I <sub>DRM</sub>	V <sub>DRM</sub> = Rated, R <sub>G</sub> = 20kΩ	-	-	10 <sup>-6</sup>	A
	*5Repetitive peak reverse current	I <sub>R<sub>RM</sub></sub>	V <sub>R<sub>RM</sub></sub> = Rated, R <sub>G</sub> = 20kΩ	-	-	10 <sup>-6</sup>	A
	ON-state voltage	V <sub>T</sub>	I <sub>T</sub> = 200mA	-	1.0	1.4	V
	Holding current	I <sub>H</sub>	V <sub>D</sub> = 6V, R <sub>G</sub> = 20kΩ	-	0.2	1	mA
	Critical rate of rise of OFF-state voltage	dV/dt	V <sub>DRM</sub> = 1/√2 Rated, R <sub>G</sub> = 20kΩ	5	-	-	V/μs
	3			-	-		
Transfer characteristics	Minimum trigger current	I <sub>FT</sub>	V <sub>D</sub> = 6V, R <sub>L</sub> = 100Ω, R <sub>G</sub> = 20kΩ	-	-	10	mA
	Isolation resistance	R <sub>ISO</sub>	DC500V, 40 to 60% RH	5 x 10 <sup>10</sup>	10 <sup>11</sup>	-	Ω
	Turn-on time	t <sub>on</sub>	V <sub>D</sub> = 6V, R <sub>G</sub> = 20kΩ, R <sub>L</sub> = 100Ω, I <sub>F</sub> = 30mA	-	20	50	μs

\*5 Applies only to **S22MD1V**

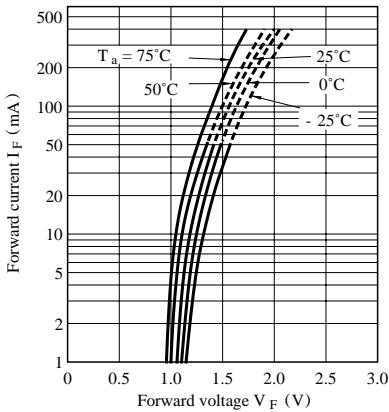
**Fig. 1 RMS ON-state Current vs. Ambient Temperature**



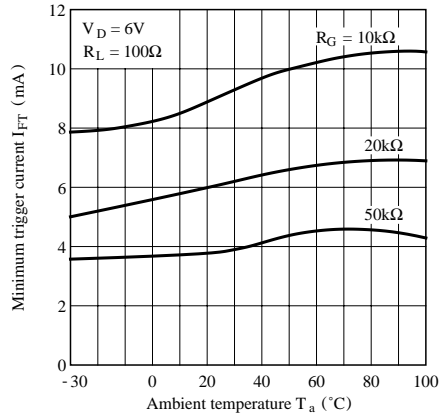
**Fig. 2 Forward Current vs. Ambient Temperature**



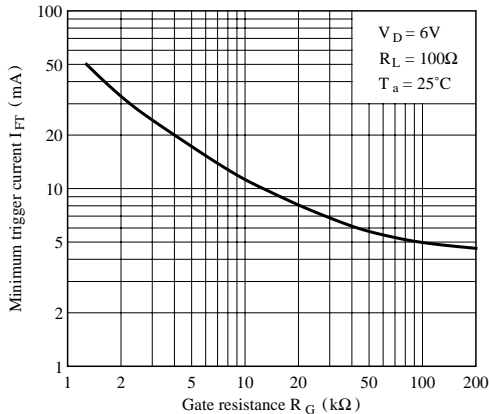
**Fig. 3 Forward Current vs. Forward Voltage**



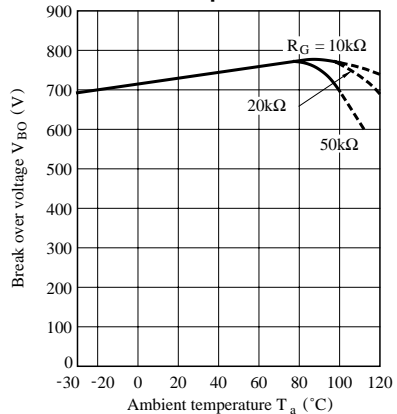
**Fig. 4 Minimum Trigger Current vs. Ambient Temperature**



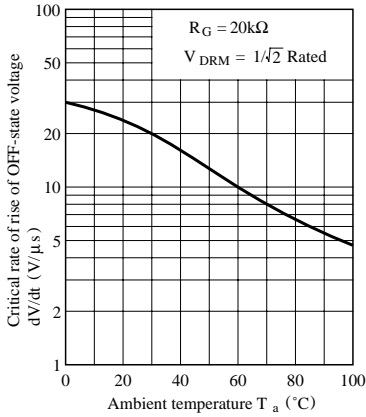
**Fig. 5 Minimum Trigger Current vs. Gate Resistance**



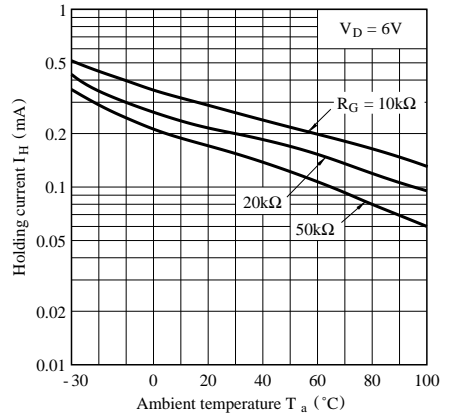
**Fig. 6 Break Over Voltage vs. Ambient Temperature**



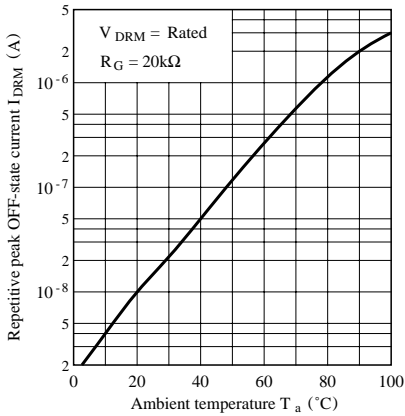
**Fig. 7 Critical Rate of Rise of OFF-state Voltage vs. Ambient Temperature**



**Fig. 8 Holding Current vs. Ambient Temperature**



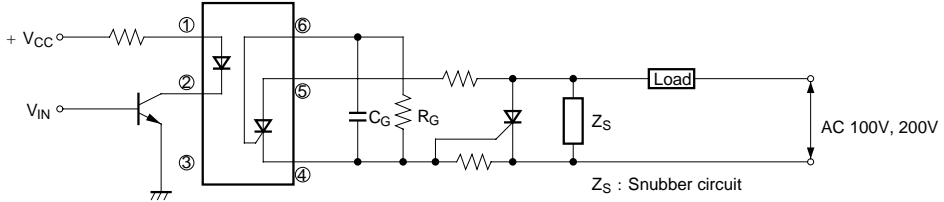
**Fig. 9 Repetitive Peak OFF-state Current vs. Ambient Temperature**



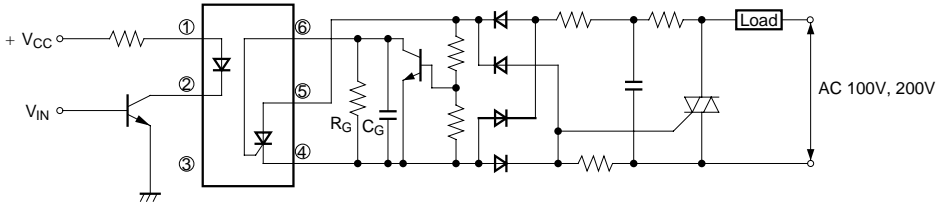
■ Basic Operation Circuit

● S22MD1V

Medium/High Power Thyristor Drive Circuit

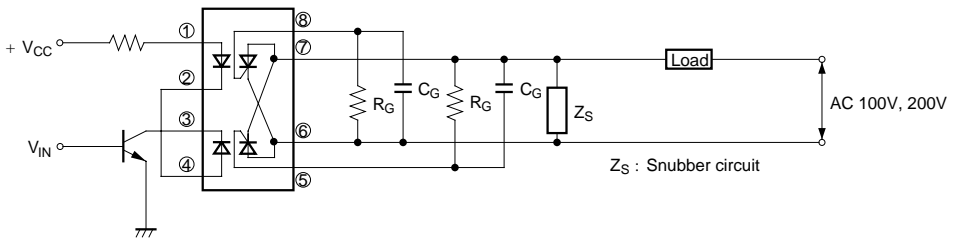


Medium/High Power Triac Drive Circuit (Zero-cross Operation)

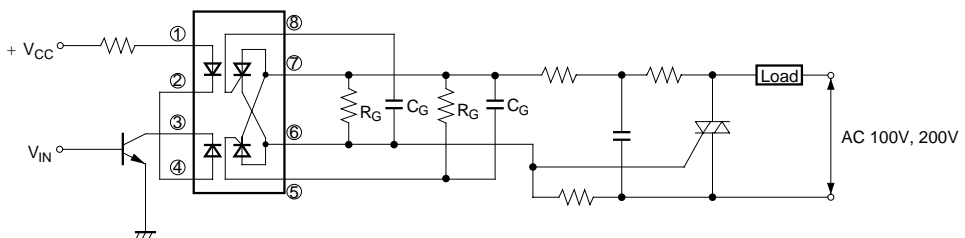


● S22MD3

Low Power Load Drive Circuit



Medium/High Power Triac Drive Circuit



● Please refer to the chapter “Precautions for Use” (Page 78 to 93).